

ABSTRACT

The invention provides a method of fabricating a thermoelectric device, whereby a grooved block (11) composed of n-type thermoelectric semiconductor and a grooved block (21) composed of p-type thermoelectric semiconductor, provided with a plurality of grooves (16, 26) formed therein, respectively, at a same pitch and parallel with each other, are formed such that a depthwise portion of respective grooved blocks is left intact, and then, an integrated block (3) is formed by fitting and adhering together the grooved blocks (11, 21) composed of the n-type and p-type thermoelectric semiconductors, respectively, filling up gaps in fitting parts with adhesive insulation members. After removing portions of the integrated block (3), other than the fitting parts where the n-type and p-type thermoelectric semiconductors are fitted to each other, n-type and p-type thermoelectric semiconductor pieces are exposed, and by forming electrodes for connecting the pieces to each other alternately and in series, the thermoelectric device is completed. Further, it is preferable to apply a process of exposing the thermoelectric semiconductor pieces and a process of forming the electrodes after applying a process of forming grooves to the integrated block (3) such that a plurality of grooves are formed in the direction crossing the direction in which the grooves (16, 26) have been formed, leaving a depthwise portion of the integrated block (3) intact, and insulation members filling up the grooves thus formed are solidified.